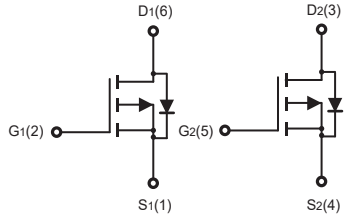
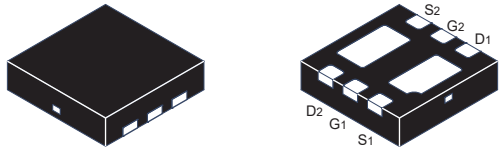
CEC2327

Dual P-Channel Enhancement Mode Field Effect Transistor

FEATURES

- -20V, -7.3A, $R_{DS(ON)}$ = 48mΩ @V_{GS} = -4.5V.
  $R_{DS(ON)}$ = 67mΩ @V_{GS} = -2.5V.
  $R_{DS(ON)}$ = 100mΩ @V_{GS} = -1.8V.
- Super High dense cell design for extremely low $R_{DS(ON)}$.
- High power and current handing capability.
- Pb-free lead plating ; RoHS compliant.
- Halogen Free.





DFN2*2

ABSOLUTE MAXIMUM RATINGS T_C = 25°C unless otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current-Continuous	I_D @$R_{\theta JC}$	-7.3	A
	I_D @$R_{\theta JA}$	-5.1	A
Drain Current-Pulsed [a]	I_D @$R_{\theta JC}$	-29.2	A
	I_D @$R_{\theta JA}$	-20.4	A
Maximum Power Dissipation	P_D	4.1	W
Operating and Store Temperature Range	T_J,T_{stg}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Limit	Units
Thermal Resistance, Junction-to-Case [b]	$R_{\theta JC}$	30	°C/W
Thermal Resistance, Junction-to-Ambient [b]	$R_{\theta JA}$	62.5	°C/W

Electrical Characteristics T_C = 25°C unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} = 0V, I_D = -250μA	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -20V, V_{GS} = 0V			-1	μA
Gate Body Leakage Current, Forward	I_{GSSF}	V_{GS} = 12V, V_{DS} = 0V			100	nA
Gate Body Leakage Current, Reverse	I_{GSSR}	V_{GS} = -12V, V_{DS} = 0V			-100	nA
On Characteristics [b]						
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS} = V_{DS}, I_D = -250μA	-0.4		-1.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = -4.5V, I_D = -5A		35	48	mΩ
		V_{GS} = -2.5V, I_D = -2.5A		48	67	mΩ
		V_{GS} = -1.8V, I_D = -1.3A		72	100	mΩ
Gate input resistance	R_g	f=1MHz,open Drain		6.4		Ω
Dynamic Characteristics [c]						
Input Capacitance	C_{iss}	V_{DS} = -10V, V_{GS} = 0V, f = 1.0 MHz		675		pF
Output Capacitance	C_{oss}			105		pF
Reverse Transfer Capacitance	C_{rss}			85		pF
Switching Characteristics [c]						
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = -10V, I_D = -3.8A, V_{GS} =-4.5V,R_{GEN} = 3Ω		11		ns
Turn-On Rise Time	t_r			5		ns
Turn-Off Delay Time	$t_{d(off)}$			35		ns
Turn-Off Fall Time	t_f			7		ns
Total Gate Charge	Q_g	V_{DS} = -10V, I_D = -3.8A, V_{GS} = -4.5V		8.7		nC
Gate-Source Charge	Q_{gs}			0.7		nC
Gate-Drain Charge	Q_{gd}			2.6		nC
Drain-Source Diode Characteristics and Maximun Ratings						
Drain-Source Diode Forward Current	I_S				-3.7	A
Drain-Source Diode Forward Voltage [b]	V_{SD}	V_{GS} = 0V, I_S = -1A			-1.1	V

Notes :
a.Repetitive Rating : Pulse width limited by maximum junction temperature
b.Pulse Test : Pulse Width < 300μs, Duty Cycle < 2%.
c.Guaranteed by design, not subject to production testing.

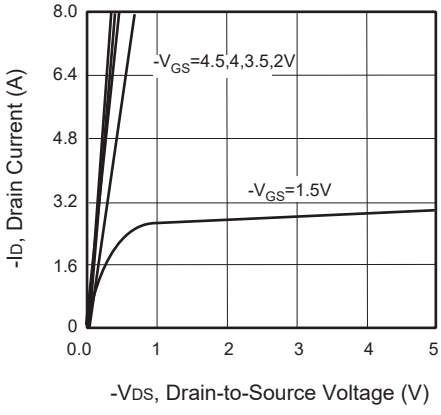


Figure 1. Output Characteristics

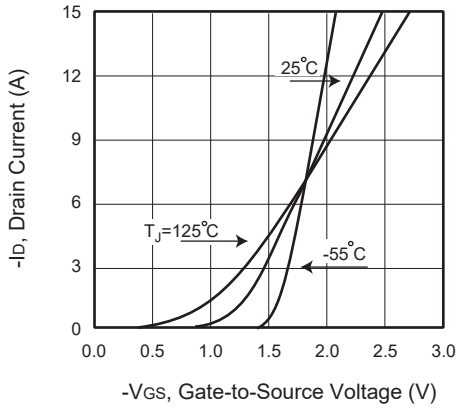


Figure 2. Transfer Characteristics

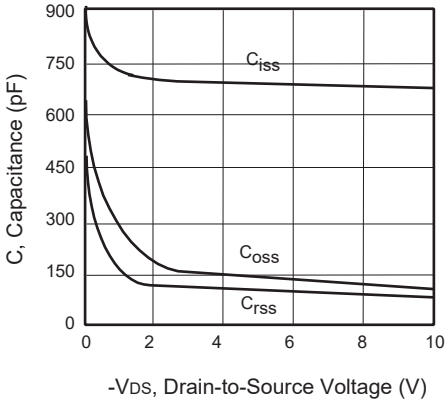


Figure 3. Capacitance

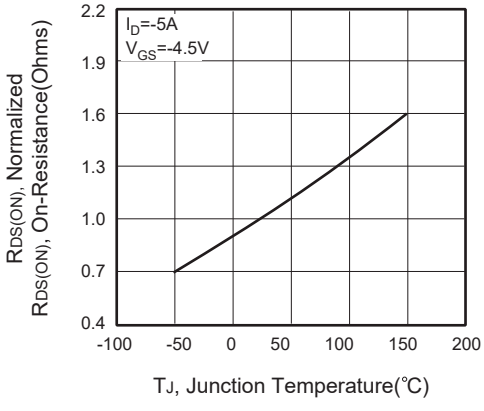


Figure 4. On-Resistance Variation with Temperature

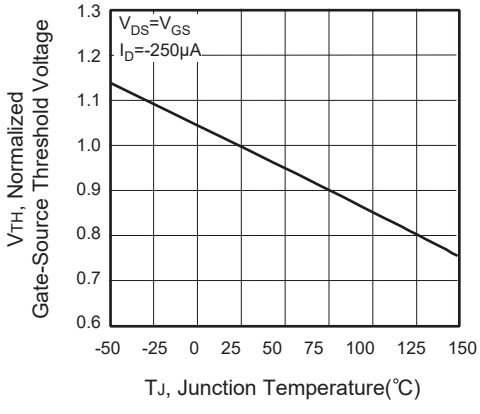


Figure 5. Gate Threshold Variation with Temperature

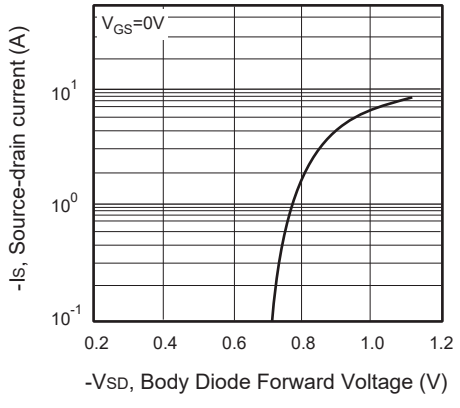


Figure 6. Body Diode Forward Voltage Variation with Source Current

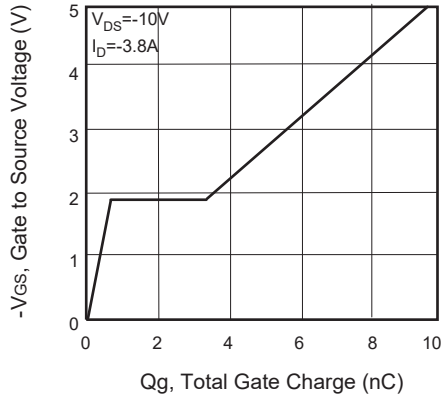


Figure 7. Gate Charge

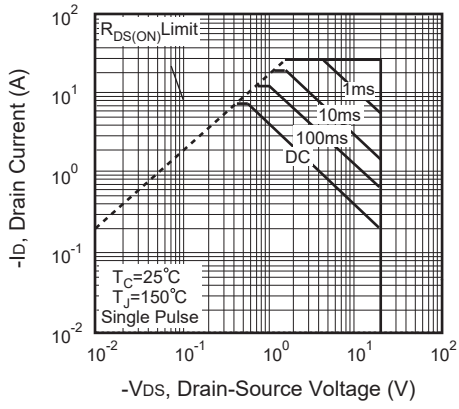


Figure 8. Maximum Safe Operating Area

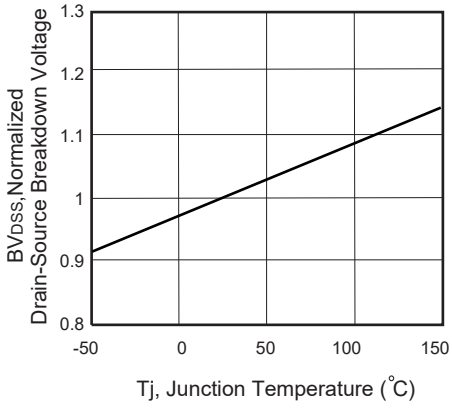


Figure 9. Breakdown Voltage Variation VS Temperature

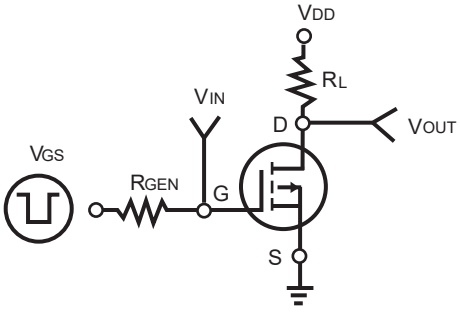


Figure 10. Switching Test Circuit

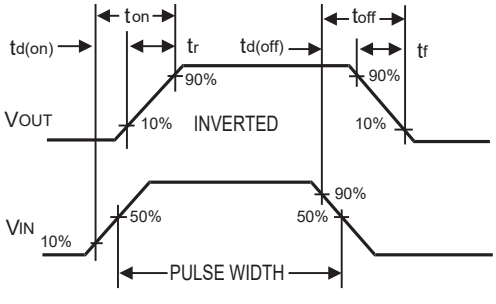


Figure 11. Switching Waveforms

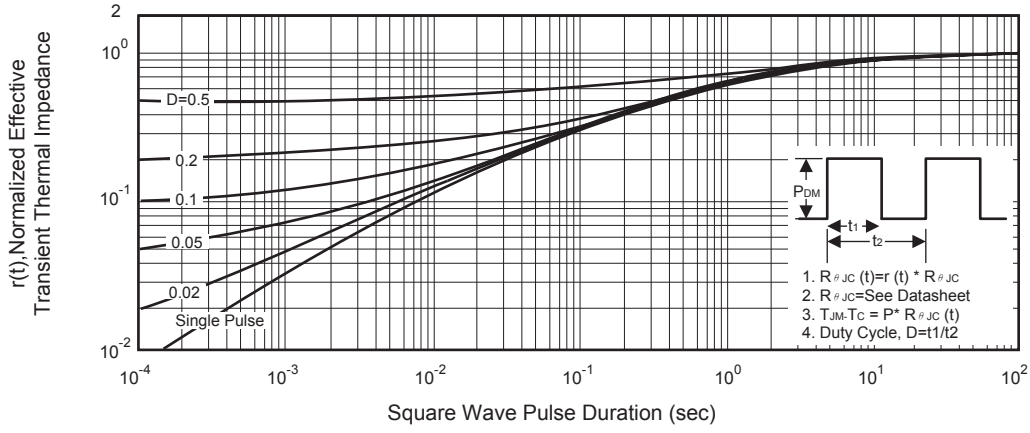
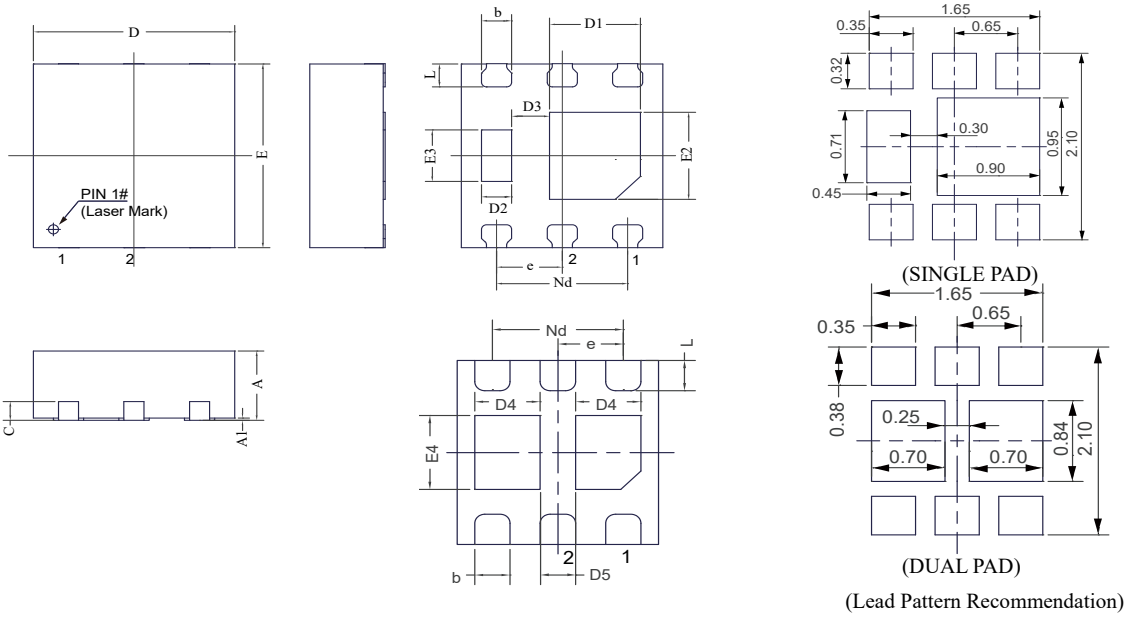


Figure 12. Normalized Thermal Transient Impedance Curve

DFN 2X2 產品外觀尺寸圖 (Product Outline Dimension)



(Lead Pattern Recommendation)

SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.500	0.800	0.020	0.031
A1	0.000	0.050	0.000	0.002
b	0.250	0.400	0.010	0.016
c	0.100	0.203	0.004	0.008
D	1.900	2.100	0.075	0.083
D1	0.850	0.950	0.033	0.037
D2	0.250	0.350	0.010	0.014
D3	0.330	0.430	0.013	0.017
D4	0.550	0.750	0.022	0.029
D5	0.250	0.450	0.010	0.018
e	0.65(BSC)		0.026(BSC)	
Nd	1.30(BSC)		0.051(BSC)	
E	1.900	2.100	0.075	0.082
E2	0.900	1.000	0.035	0.039
E3	0.510	0.710	0.020	0.028
E4	0.750	0.960	0.030	0.038
L	0.200	0.380	0.008	0.015